

ABSTRACT

RINSE SOLUTION FOR LITHOGRAPHY AND METHOD FOR FORMING RESIST PATTERN USING THE SAME

Disclosed are a rinse solution for lithography comprising water and a nonionic surfactant represented by the formula (I) (R_1 and R_2 may be the same as or different from each other and represent a hydrogen atom or a methyl group, R_3 and R_4 may be the same as or different from each other and represent a hydrogen atom, a methyl group or an ethyl group, R_5 represents a hydrocarbon group having 2 to 5 carbon atoms, in which one or more of a double bond or triple bond are contained, or a phenylene group, and R_6 and R_7 may be the same as or different from each other and represent a hydrogen atom or a methyl group) and a method for forming a resist pattern by rinsing the resist pattern obtained by exposing and developing a photosensitive resist with the rinse solution for lithography described above.

